Yoriko Tominaga

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/6105753/publications.pdf

Version: 2024-02-01

19 papers	269 citations	1307594 7 h-index	1058476 14 g-index
19 all docs	19 docs citations	19 times ranked	226 citing authors

#	Article	IF	Citations
1	Crystalline quality of GaAs_{1â^'x}Bi_x grown below 250 Â°C using molecular beam epitaxy. Applied Physics Express, 2022, 15, 045504.	2.4	0
2	Structural evaluation of low-temperature-grown InGaAs crystals on (0 0 1) InP substrates. Journal of Crystal Growth, 2020, 548, 125852.	1.5	2
3	Crystalline quality of low-temperature-grown In Ga1â^'As coherently grown on InP(0ÂÂ0Â1) substrate. Journal of Crystal Growth, 2020, 544, 125703.	1.5	2
4	Optical readout of hydrogen storage in films of Au and Pd. Optics Express, 2017, 25, 24081.	3.4	24
5	Recent Advancement of Semiconductor Materials and Devices. Zairyo/Journal of the Society of Materials Science, Japan, 2017, 66, 185-191.	0.2	0
6	Effect of thermal annealing on the crystallization of low-temperature-grown In0.42Ga0.58As on InP substrate. Japanese Journal of Applied Physics, 2016, 55, 110313.	1.5	1
7	Crystal structure of low-temperature-grown In0.45Ga0.55As on an InP substrate. Journal of Crystal Growth, 2015, 425, 99-101.	1.5	6
8	Breaking Bullseyeâ€™s Symmetry for Axial Field Focusing. Journal of Infrared, Millimeter, and Terahertz Waves, 2015, 36, 455-460.	2.2	0
9	Quantitative estimation of density of Bi-induced localized states in GaAs1â^'xBix grown by molecular beam epitaxy. Journal of Crystal Growth, 2013, 378, 73-76.	1.5	32
10	Photo-pumped GaAs 1&-x Bi x lasing operation with low-temperature-dependent oscillation wavelength. Proceedings of SPIE, 2012, , .	0.8	3
11	Deep-Hole Traps in p-Type GaAs_{1-x}Bi_x Grown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 080203.	1.5	22
12	Temperature-insensitive photoluminescence emission wavelength in GaAs1-xBix/GaAs multiquantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 260-262.	0.8	8
13	Deep-Hole Traps in p-Type GaAs_{1-x}Bi_xGrown by Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 080203.	1.5	2
14	Low Temperature Dependence of Oscillation Wavelength in GaAs_{1-x}Bi_xLaser by Photo-Pumping. Applied Physics Express, 2010, 3, 062201.	2.4	90
15	Growth of GaAs_{1-x}Bi_x/Al_yGa_{1-y}As Multi-Quantum-Well Structures. Japanese Journal of Applied Physics, 2010, 49, 070211.	1.5	5
16	Lasing in GaAs<inf>1−x</inf>Bi<inf>x</inf>/GaAs thin film cavity with low-temperature-dependent oscillation wavelength. , 2010, , .		0
17	Growth of GaAs_{1â€“x}Bi_x/GaAs multiâ€quantum wells by molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 2719-2721.	0.8	9
18	Structural investigation of GaAs1â^'xBix/GaAs multiquantum wells. Applied Physics Letters, 2008, 93, 131915.	3.3	60

#	Article	IF	Citations
19	Growth of InPBi on InP(311)B substrate by molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100411.	1.8	3